

REMARKS

In response to the Examiner's Advisory Action of October 23, 2003 and the telephonic interview with the Examiner on October 29, 2003, independent claims 12, 18, 23, 29, 34, 37, 41, 53, 55, and 58 have been amended, as shown above.

As discussed during the interview, the Examiner's reasoning for maintaining the rejections made in the Office Action of May 29, 2003 is that Fig. 5G of Yamazaki shows crystallized regions 6S and 6D that occur below gate 5G. Hence, the Examiner interprets the drawing as channel region 5C as partially crystallized. Further, the Examiner asserts that the language of "crystallizing at least a channel formation region", found in claim 12, for example, is rendered obvious by Yamazaki as explained above.

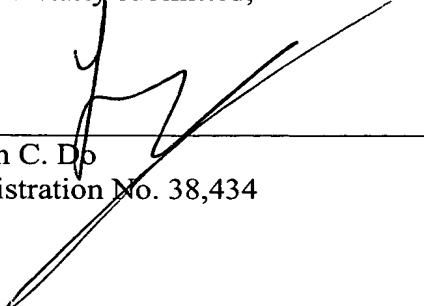
In response to the Examiner's assertions, Applicants submitted that the entire channel formation region is crystallized, and the language "at least" found in, e.g., claim 12, means that the source and drain region may also be crystallized. Further, Applicants proposed amending the claims to read as "crystallizing at least an entire channel formation region of said semiconductor film by laser irradiation through said insulating film"; and, an agreement was reached with the Examiner that such an amendment will overcome the cited prior art references to Yamazaki (U.S. Patent 4,727,044) and Mukai (U.S. Patent 5,077,233).

As a result of the interview, Applicants have amended all of the pending independent claims, as shown above. Accordingly, all the pending 35 U.S.C. §103(a) rejections of pending claims 12, 13, 15-19, 21-24, 26-43, 46-58, 60, 61, 65-71 and 75-96 are respectfully requested to be reconsidered and withdrawn.

While the present application is now believed to be in condition for allowance, should the Examiner find some issue to remain unresolved, or should any issues arise, which could

be eliminated through discussions with Applicants' representative, then the Examiner is invited to contact the undersigned by telephone in order that the further prosecution of this application can thereby be expedited.

Respectfully submitted,


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